

3-Phase Bridge Rectifier + IGBT braking chopper

SKD 146/-L140

Target Data

Features

- · Compact design
- Two screws mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- High surge currents
- 1600V reverse voltage
- UL recognized, file no. E 63 532
- Integrated PTC temperature sensor
- Remarks: V_{CE,sat}, V_F = chip level value

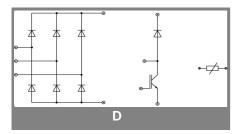
Typical Applications*

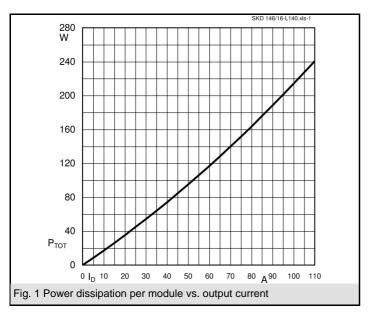
- · DC drives
- Controlled filed rectifiers for DC motors
- · Controlled battery charger

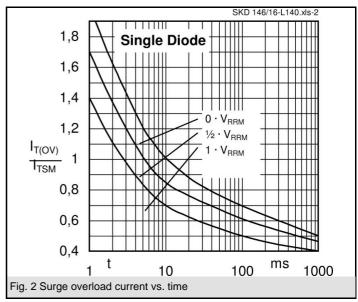
V_{RSM}	V_{RRM}, V_{DRM}	I _D = 140 A (maximum value for continuous operation)			
V	V	(T _s = 85 °C)			
1300	1200	SKD146/12-L140			
1700	1600	SKD146/16-L140			

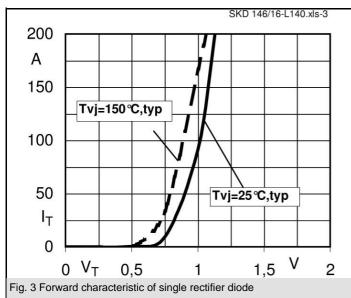
Absolute Maximum Ratings T _s = 25 °C, unless otherwise specifie							
Symbol	Conditions	Values	Units				
Bridge - Rectifier							
I _D	T _s = 85 °C; inductive load	140	Α				
I_{FSM}/I_{TSM}	$t_p = 10 \text{ ms}; \sin 180^\circ; T_{jmax}$	1250	Α				
i²t	$t_p = 10 \text{ ms}; \sin 180^\circ; T_{jmax}$	7800	A²s				
IGBT - Chopper							
V_{CES}/V_{GES}		1200 / 20	V				
I _C	T _s = 25 (70) °C	165 (110)	Α				
I _{CM}	$t_p = 1 \text{ ms; } T_s = 25 (70) ^{\circ}\text{C}$	330 (220)	Α				
Freewhee	eling - CAL Diode						
V_{RRM}		1200	V				
I_{F}	T _s = 25 (70) °C	130 (90)	Α				
I _{FM}	$t_p = 1 \text{ ms; } T_s = 25 (70) ^{\circ}\text{C}$	240 (180)	Α				
T_{v_i}	Diode & IGBT (Thyristor)	- 40 + 150 (0 + 125)	°C				
T _{stg}		- 40 + 125	°C				
T _{solder}	terminals, 10 s	260	°C				
V _{isol}	a.c. (50) Hz, RMS 1 min. / 1 s	3000 / 3600	V				

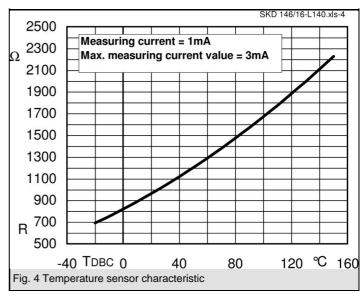
Characteristics		T _s = 25 °C, unless otherwise specified				
Symbol	Conditions	min.	typ.	max.	Units	
Diode - Rectifier						
V_{TO} / r_{t}	T _j = 125 °C		0,8 / 4		V / $m\Omega$	
$R_{th(j-s)}$	per diode			0,8	K/W	
IGBT - Chopper						
V _{CE(sat)}	I _C = 140 A, T _j = 25 °C; V _{GE} = 15 V		1,65	2,05	V	
$R_{th(j-s)}$	per IGBT			0,35	K/W	
t _{d(on)} / t _r	valid for all values:		118 / 104		ns	
t _{d(off)} / t _f	V _{CC} = 600 V; V _{GE} = 15 V; I _C = 140 A; T _j = 125 °C;		1008 / 95		ns	
$E_{on}+E_{off}$	$T_{j} = 125 ^{\circ}\text{C}; R_{G} = 22 \Omega;$		64		mJ	
	inductive load					
CAL - Diode - Freewheeling						
$V_{T(TO)} / r_t$	T _j = 125 °C		0,8 / 5	0,9 / 5,7	V / $m\Omega$	
$R_{th(j-s)}$	per diode			0,6	K/W	
I _{RRM}	valid for all values:		40		Α	
Q _{rr}	$I_F = 140 \text{ A}; V_R = -600 \text{ V};$ $dI_F/dt = -1000 \text{ A}/\mu\text{s}$		20		μC	
E _{off}	V _{GE} = 0 V; T _j = 125 °C		8,8		mJ	
Temperature Sensor						
R _{TS}	T = 25 (100) °C;		1000 (1670)		Ω	
Mechanical data						
M_S	mounting Torque	2,55		3,45	Nm	

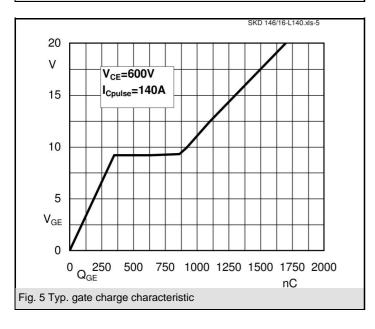


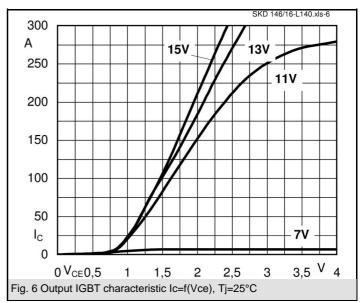


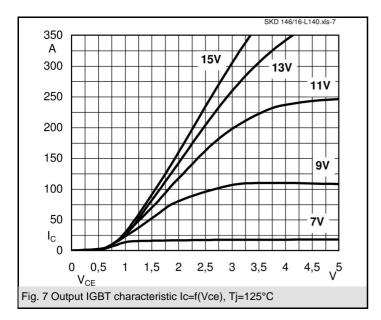


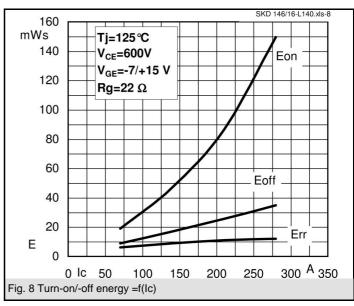


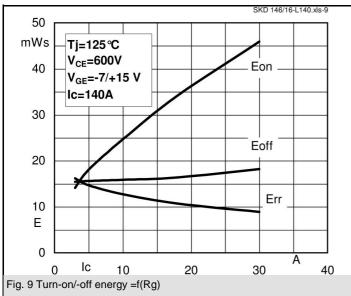


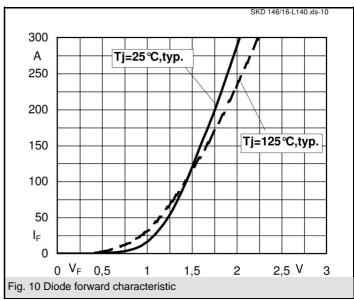


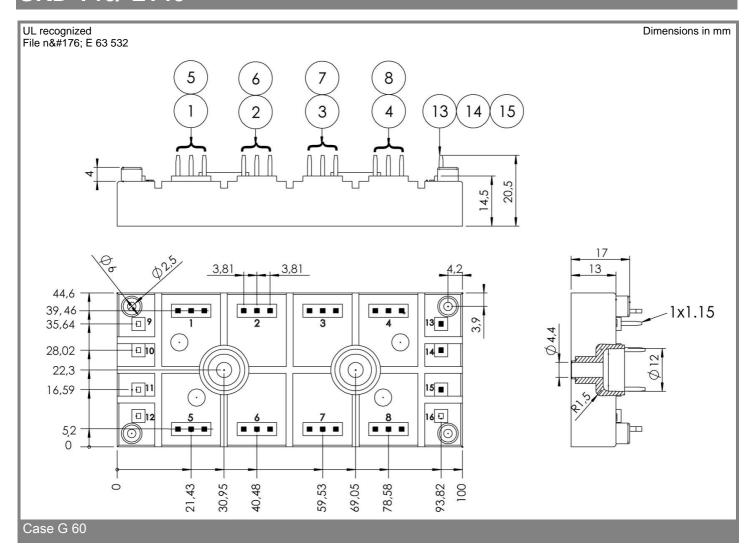


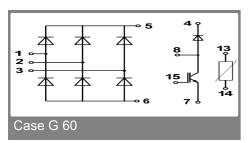












This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

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